# onsemi

## **General Purpose Transistors**

**NPN Silicon** 

## MMBT2222L, MMBT2222AL, SMMBT2222AL

#### Features

- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant
- S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable

#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector – Emitter Voltage MMBT2222L MMBT2222AL, SMMBT2222AL	V <sub>CEO</sub>	30 40	Vdc
Collector – Base Voltage MMBT2222L MMBT2222AL, SMMBT2222AL	V <sub>CBO</sub>	60 75	Vdc
Emitter – Base Voltage MMBT2222L MMBT2222AL, SMMBT2222AL	V <sub>EBO</sub>	5.0 6.0	Vdc
Collector Current – Continuous	Ι <sub>C</sub>	600	mAdc
Collector Current – Peak (Note 3)	I <sub>CM</sub>	1100	mAdc

#### THERMAL CHARACTERISTICS

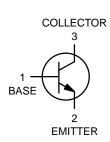
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR–5 Board (Note 1) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	225 1.8	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	556	°C/W
Total Device Dissipation Alumina Substrate (Note 2) T <sub>A</sub> = 25°C Derate above 25°C	P <sub>D</sub>	300 2.4	mW mW/°C
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	417	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. FR-5 =  $1.0 \times 0.75 \times 0.062$  in.

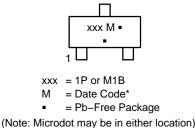
2. Alumina =  $0.4 \times 0.3 \times 0.024$  in. 99.5% alumina.

3. Reference SOA curve.





#### MARKING DIAGRAM



\*Date Code orientation and/or overbar may vary depending upon manufacturing location.

#### ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 6 of this data sheet.

### **ELECTRICAL CHARACTERISTICS** ( $T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage ( $I_C = 10 \text{ mAdc}, I_B = 0$ )	MMBT2222 MMBT2222A	V <sub>(BR)CEO</sub>	30 40	- -	Vdc
Collector – Base Breakdown Voltage ( $I_C = 10 \ \mu Adc$ , $I_E = 0$ )	MMBT2222 MMBT2222A	V <sub>(BR)CBO</sub>	60 75	-	Vdc
Emitter-Base Breakdown Voltage (I <sub>E</sub> = 10 $\mu$ Adc, I <sub>C</sub> = 0)	MMBT2222 MMBT2222A	V <sub>(BR)EBO</sub>	5.0 6.0	-	Vdc
Collector Cutoff Current ( $V_{CE} = 60 \text{ Vdc}, V_{EB(off)} = 3.0 \text{ Vdc}$ ) MMBT2222A, S	MMBT2222A	I <sub>CEX</sub>	_	10	nAdc
	MMBT2222	I <sub>CBO</sub>		0.01 0.01 10 10	μAdc
Emitter Cutoff Current ( $V_{EB} = 3.0 \text{ Vdc}, I_C = 0$ ) MMBT2222A, S	MMBT2222A	I <sub>EBO</sub>	-	100	nAdc
Base Cutoff Current (V <sub>CE</sub> = 60 Vdc, V <sub>EB(off)</sub> = 3.0 Vdc) MMBT2222A, S	MMBT2222A	I <sub>BL</sub>	-	20	nAdc
ON CHARACTERISTICS					
$ \begin{array}{l} \text{DC Current Gain} \\ (I_{C} = 0.1 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}) \\ (I_{C} = 1.0 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}) \\ (I_{C} = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}) \\ (I_{C} = 10 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}, T_{A} = -55^{\circ}\text{C}) \\ (I_{C} = 150 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}) (\text{Note 4}) \\ (I_{C} = 150 \text{ mAdc}, V_{CE} = 1.0 \text{ Vdc}) (\text{Note 4}) \\ (I_{C} = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}) (\text{Note 4}) \\ (I_{C} = 500 \text{ mAdc}, V_{CE} = 10 \text{ Vdc}) (\text{Note 4}) \\ \end{array} $	3T2222A only MMBT2222 SMMBT2222A	h <sub>FE</sub>	35 50 75 35 100 50 30 40	- - 300 - -	_
Collector – Emitter Saturation Voltage (Note 4) (I <sub>C</sub> = 150 mAdc, I <sub>B</sub> = 15 mAdc) MMBT2222A, S	MMBT2222 MMBT2222A	V <sub>CE(sat)</sub>	-	0.4 0.3	Vdc
(I <sub>C</sub> = 500 mAdc, I <sub>B</sub> = 50 mAdc) MMBT2222A, S	MMBT2222 MMBT2222A		-	1.6 1.0	
Base – Emitter Saturation Voltage (Note 4) (I <sub>C</sub> = 150 mAdc, I <sub>B</sub> = 15 mAdc) MMBT2222A, S	MMBT2222 MMBT2222A	V <sub>BE(sat)</sub>	_ 0.6	1.3 1.2	Vdc
(I <sub>C</sub> = 500 mAdc, I <sub>B</sub> = 50 mAdc) MMBT2222A, S	MMBT2222 MMBT2222A		-	2.6 2.0	
SMALL-SIGNAL CHARACTERISTICS					-
Current–Gain – Bandwidth Product (Note 5) (I <sub>C</sub> = 20 mAdc, V <sub>CE</sub> = 20 Vdc, f = 100 MHz) MMBT2222A, S	MMBT2222 MMBT2222A	f <sub>T</sub>	250 300		MHz
Output Capacitance ( $V_{CB} = 10 \text{ Vdc}, I_E = 0, f = 1.0 \text{ MHz}$ )		C <sub>obo</sub>	-	8.0	pF
Input Capacitance (V <sub>EB</sub> = 0.5 Vdc, I <sub>C</sub> = 0, f = 1.0 MHz) MMBT2222A, S	MMBT2222 MMBT2222A	C <sub>ibo</sub>		30 25	pF
		h <sub>ie</sub>	2.0 0.25	8.0 1.25	kΩ
$\label{eq:Voltage Feedback Ratio} \begin{aligned} & (I_C = 1.0 \text{ mAdc}, \text{V}_{CE} = 10 \text{ Vdc}, \text{f} = 1.0 \text{ kHz}) \\ & (I_C = 10 \text{ mAdc}, \text{V}_{CE} = 10 \text{ Vdc}, \text{f} = 1.0 \text{ kHz}) \end{aligned} \qquad \begin{array}{l} \text{MMBT2222A, S} \\ & \text{MMBT2222A, S} \end{aligned}$		h <sub>re</sub>		8.0 4.0	X 10 <sup>-4</sup>
		h <sub>fe</sub>	50 75	300 375	-

#### ELECTRICAL CHARACTERISTICS (T<sub>A</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit	
SMALL-SIGNAL CHARACTERISTICS					
Output Admittance ( $I_C = 1.0 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ ) ( $I_C = 10 \text{ mAdc}$ , $V_{CE} = 10 \text{ Vdc}$ , $f = 1.0 \text{ kHz}$ )	MMBT2222A, SMMBT2222A MMBT2222A, SMMBT2222A	h <sub>oe</sub>	5.0 25	35 200	μmhos
Collector Base Time Constant ( $I_E$ = 20 mAdc, $V_{CB}$ = 20 Vdc, f = 31.8 MHz)	MMBT2222A, SMMBT2222A	rb, C <sub>c</sub>	_	150	ps
Noise Figure (I <sub>C</sub> = 100 $\mu$ Adc, V <sub>CE</sub> = 10 Vdc, R <sub>S</sub> = 1.0	kΩ, f = 1.0 kHz) MMBT2222A, SMMBT2222A	NF	-	4.0	dB
SWITCHING CHARACTERISTICS (MMBT2222A onl	y)	•			•

Delay Time	(V <sub>CC</sub> = 30 Vdc, V <sub>BE(off)</sub> = -0.5 Vdc,	t <sub>d</sub>	-	10	20
Rise Time	$I_{\rm C} = 150 \text{ mAdc}, I_{\rm B1} = 15 \text{ mAdc})$	t <sub>r</sub>	-	25	ns
Storage Time	$(V_{CC} = 30 \text{ Vdc}, I_{C} = 150 \text{ mAdc},$	t <sub>s</sub>	-	225	ns
Fall Time	$I_{B1} = I_{B2} = 15 \text{ mAdc}$	t <sub>f</sub>	-	60	115

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 4. Pulse Test: Pulse Width  $\leq$  300 µs, Duty Cycle  $\leq$  2.0%.

5.  $f_T$  is defined as the frequency at which  $|h_{fe}|$  extrapolates to unity.

#### SWITCHING TIME EQUIVALENT TEST CIRCUITS

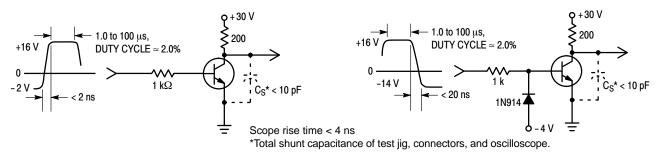
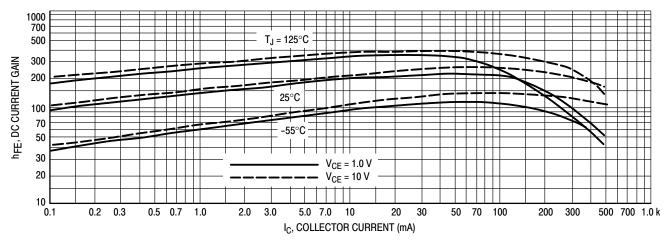
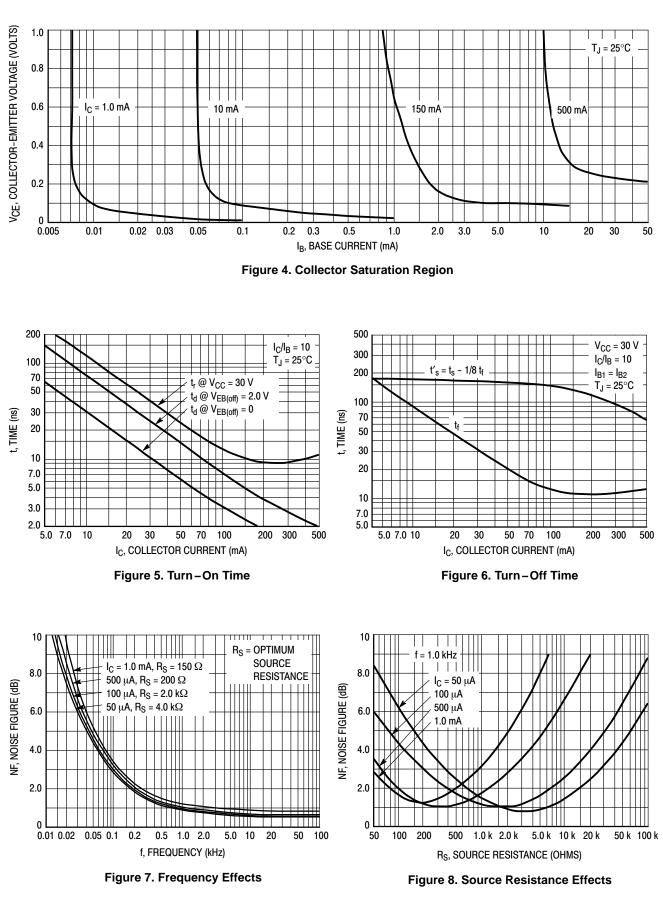


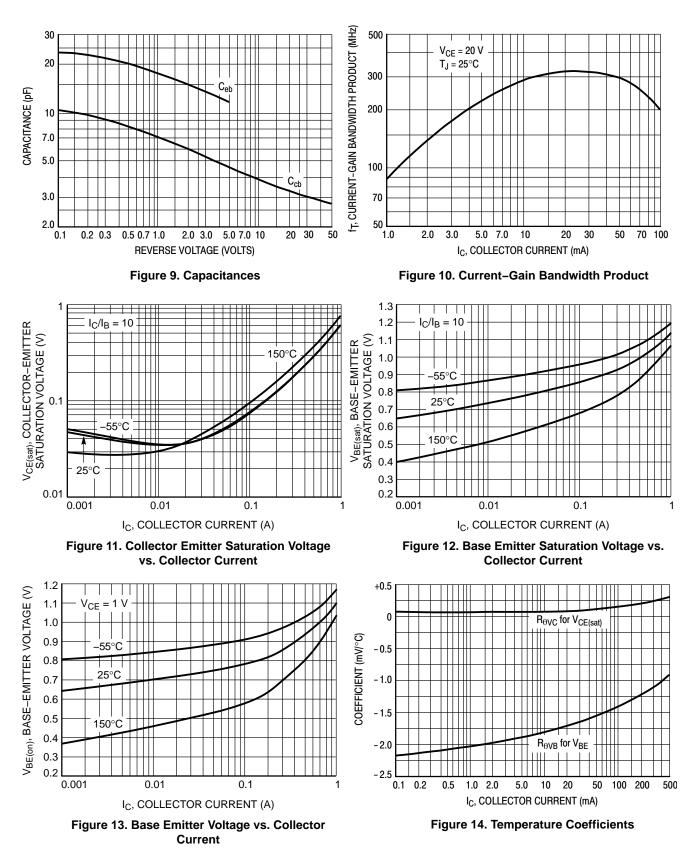


Figure 2. Turn-Off Time









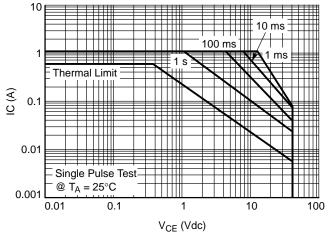


Figure 15. Safe Operating Area

#### ORDERING INFORMATION

Device	Specific Marking Code	Package	Shipping <sup>†</sup>
MMBT2222LT1G	M1B	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBT2222ALT1G, SMMBT2222ALT1G	1P	SOT-23 (Pb-Free)	3000 / Tape & Reel
MMBT2222LT3G	M1B	SOT-23 (Pb-Free)	10,000 / Tape & Reel
MMBT2222ALT3G, SMMBT2222ALT3G	1P	SOT-23 (Pb-Free)	10,000 / Tape & Reel

+For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

\*S Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC–Q101 Qualified and PPAP Capable.

#### **MECHANICAL CASE OUTLINE** PACKAGE DIMENSIONS

D

3

TOP VIEW

SIDE VIEW

Нe

DETAIL A

-3X b

# DUSem



SCALE 4:1

Α A1SOT-23 (TO-236) **CASE 318 ISSUE AT** 

0.25

-L1

DETAIL A

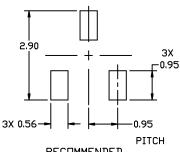
END VIEW

DATE 01 MAR 2023

NDTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- CONTROLLING DIMENSION: MILLIMETERS 2.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS DF THE BASE MATERIAL. З.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. 4.

	MILLIM	IETERS			INCHES	
DIM	MIN.	NDM.	MAX.	MIN.	NDM.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
с	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
Η <sub>E</sub>	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10*	0*		10*



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D. \*

GENERIC **MARKING DIAGRAM\*** 



XXX = Specific Device Code

М = Date Code

= Pb-Free Package .

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

#### **STYLES ON PAGE 2**

DOCUMENT NUMBER:	98ASB42226B	Electronic versions are uncontrolled except when accessed directly from the Document Repositor Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.			
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## MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

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#### SOT-23 (TO-236) CASE 318 ISSUE AT

#### DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE		
STYLE 9:	STYLE 10:	STYLE 11:	STYLE 12:	STYLE 13:	STYLE 14:
PIN 1. ANODE	PIN 1. DRAIN	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. SOURCE	PIN 1. CATHODE
2. ANODE	2. SOURCE	2. CATHODE	2. CATHODE	2. DRAIN	2. GATE
3. CATHODE	3. GATE	3. CATHODE-ANODE	3. ANODE	3. GATE	3. ANODE
STYLE 15:	STYLE 16:	STYLE 17:	STYLE 18:	STYLE 19:	STYLE 20:
PIN 1. GATE	PIN 1. ANODE	PIN 1. NO CONNECTION	PIN 1. NO CONNECTION	PIN 1. CATHODE	PIN 1. CATHODE
2. CATHODE	2. CATHODE	2. ANODE	2. CATHODE	2. ANODE	2. ANODE
3. ANODE	3. CATHODE	3. CATHODE	3. ANODE	3. CATHODE-ANODE	3. GATE
STYLE 21:	STYLE 22:	STYLE 23:	STYLE 24:	STYLE 25:	STYLE 26:
PIN 1. GATE	PIN 1. RETURN	PIN 1. ANODE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE
2. SOURCE	2. OUTPUT	2. ANODE	2. DRAIN	2. CATHODE	2. ANODE
3. DRAIN	3. INPUT	3. CATHODE	3. SOURCE	3. GATE	3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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